



BTA420X-800BT

3Q Hi-Com Triac

5 June 2014

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series BT" triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ °C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- High voltage capability
- Isolated mounting base package
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Applications subject to high temperature
- Heating controls
- High power motor control
- High power switching

4. Quick reference data

Table 1. Quick reference data

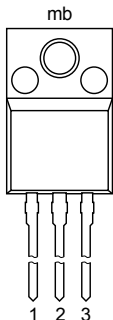
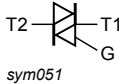
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------|--------------------------------------|---|-----|-----|-----|------|
| V_{DRM} | repetitive peak off-state voltage | | - | - | 800 | V |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | - | 200 | A |
| T_j | junction temperature | | - | - | 150 | °C |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_h \leq 50\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 20 | A |



| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|------|-----|-----|------|
| Static characteristics | | | | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7 | - | - | 50 | mA |
| | | V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7 | - | - | 50 | mA |
| | | V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7 | - | - | 50 | mA |
| Dynamic characteristics | | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit | 1800 | - | - | V/μs |
| dI _{com} /dt | rate of change of commutating current | V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 20 A; dV _{com} /dt = 10 V/μs; gate open circuit | 25 | - | - | A/ms |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--|---|
| 1 | T1 | main terminal 1 |  <p>TO-220F (SOT186A)</p> |  <p>sym051</p> |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|---------|---|---------|
| | Name | Description | Version |
| BTA420X-800BT | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

7. Marking

Table 4. Marking codes

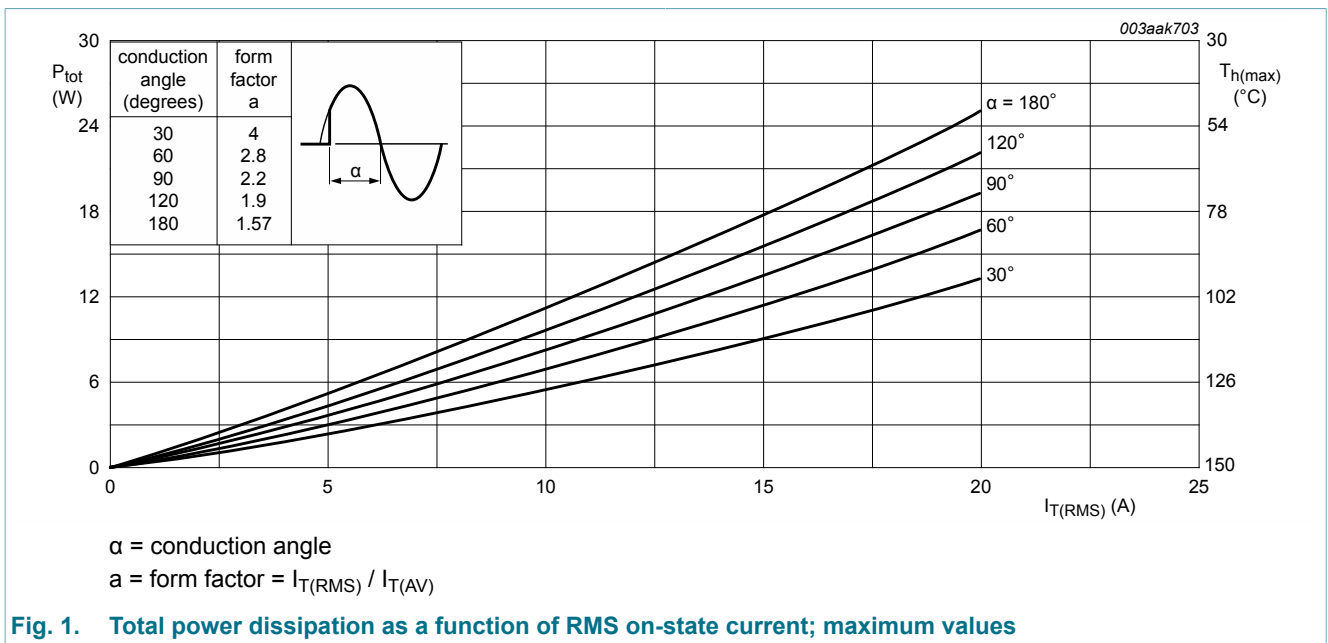
| Type number | Marking code |
|---------------|---------------|
| BTA420X-800BT | BTA420X-800BT |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------|--------------------------------------|---|-----|-----|-------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_h \leq 50\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | - | 20 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | - | 200 | A |
| | | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | - | 220 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; sine-wave pulse | - | 200 | A^2s |
| di_T/dt | rate of rise of on-state current | $I_T = 24\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A/s}$ | - | 100 | $A/\mu s$ |
| I_{GM} | peak gate current | | - | 2 | A |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T_{stg} | storage temperature | | -40 | 150 | $^{\circ}C$ |
| T_j | junction temperature | | - | 150 | $^{\circ}C$ |



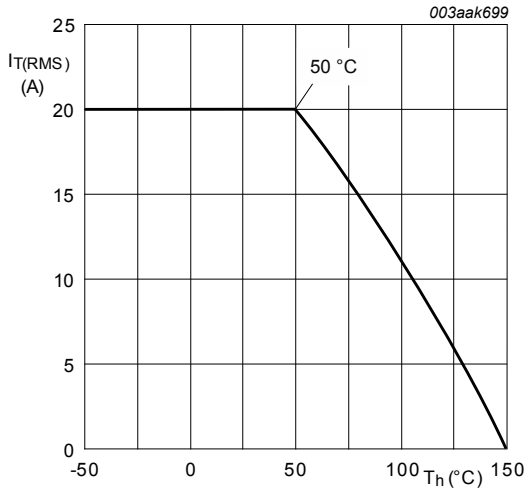
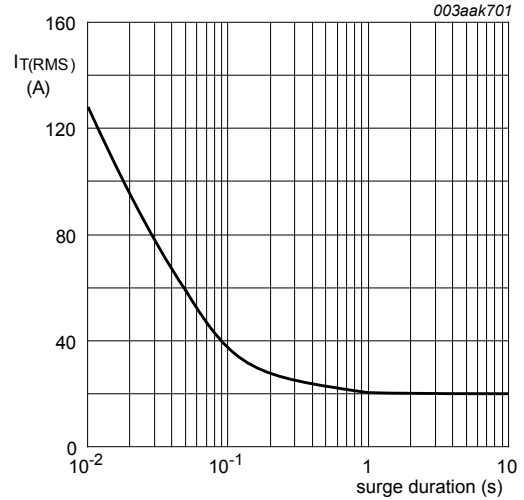
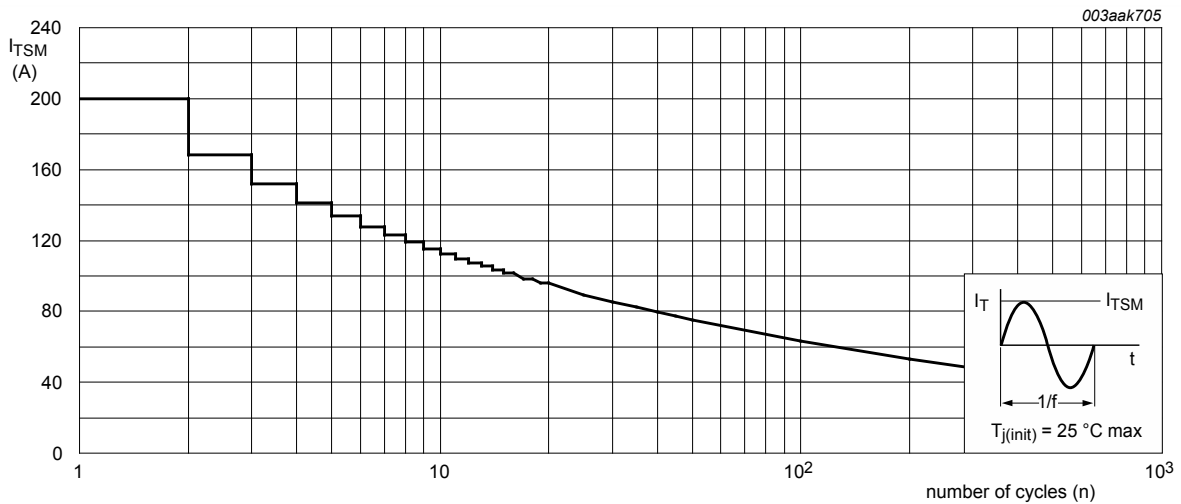


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



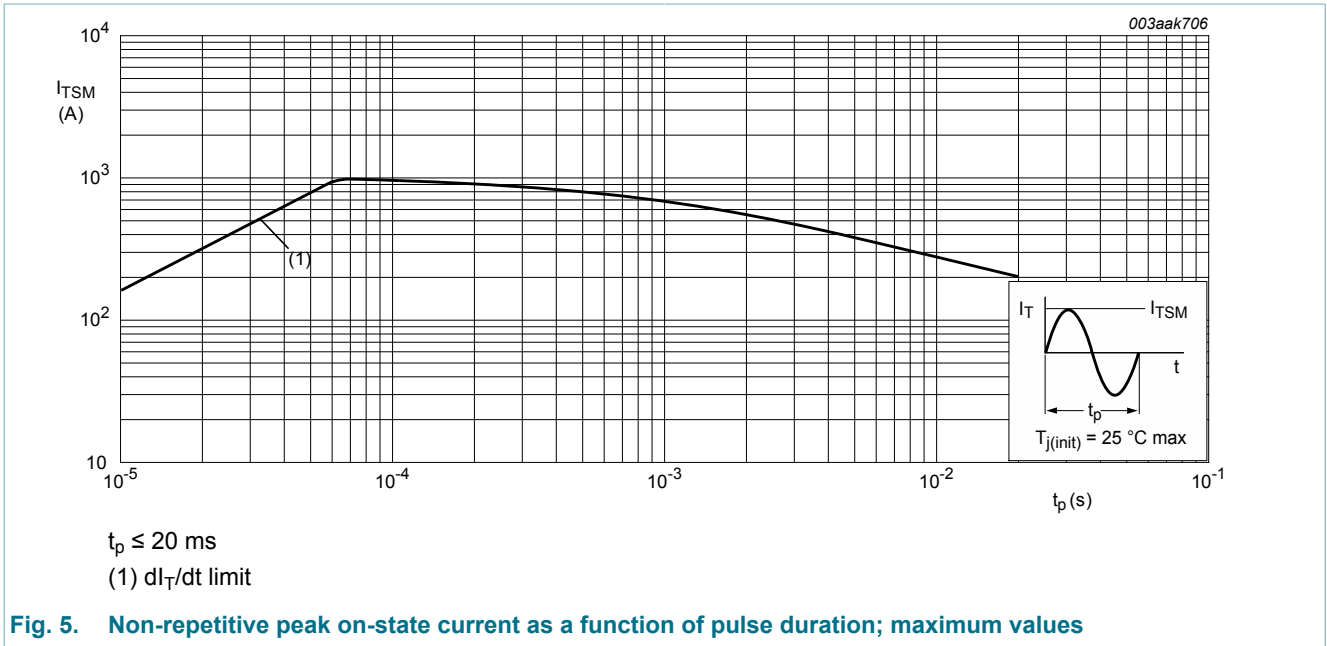
$f = 50 \text{ Hz}; T_h = 50 \text{ °C}$

Fig. 3. RMS on-state current as a function of surge duration; maximum values



$f = 50 \text{ Hz}$

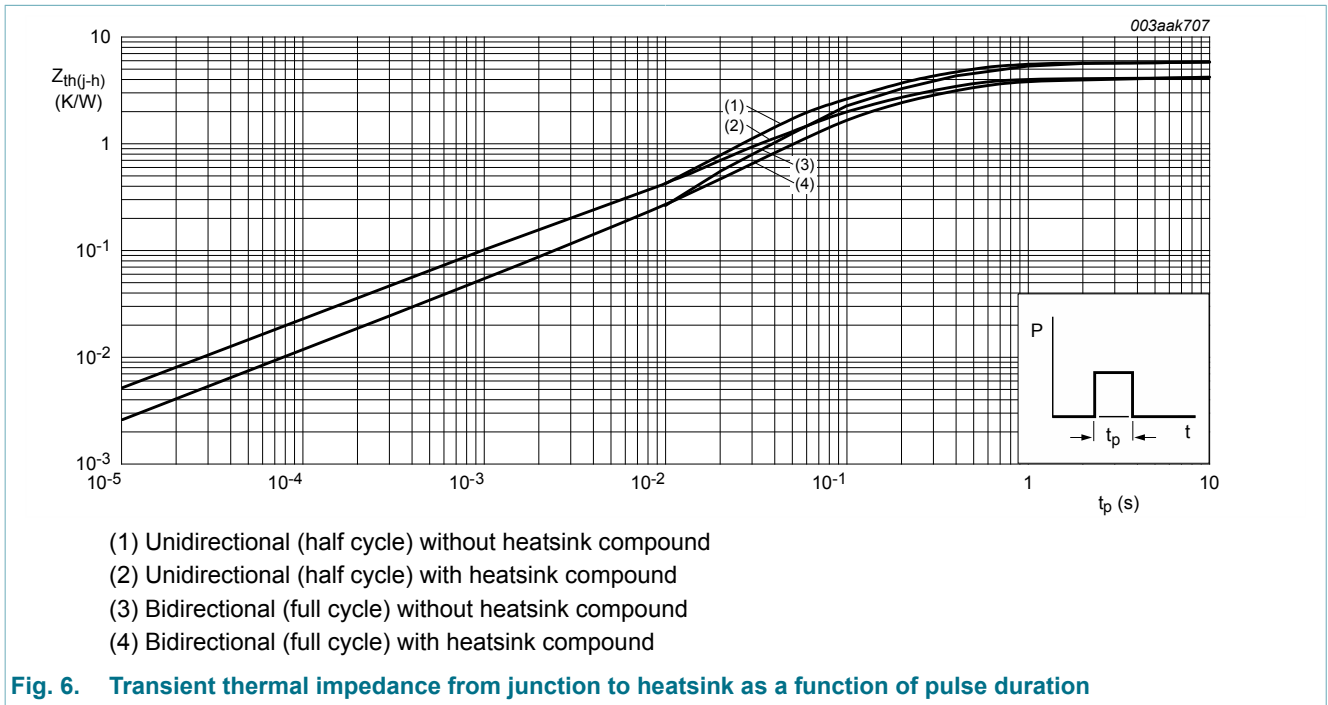
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|---|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | full cycle or half cycle; with heatsink compound; Fig. 6 | - | - | 4 | K/W |
| | | full cycle or half cycle; without heatsink compound; Fig. 6 | - | - | 5.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | - | 55 | - | K/W |



10. Isolation characteristics

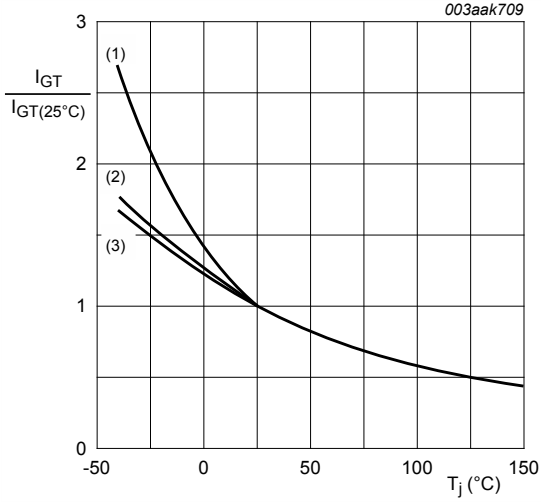
Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|--|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$; $RH \leq 65\%$; $T_h = 25\text{ }^\circ\text{C}$ | - | - | 2500 | V |
| C_{isol} | isolation capacitance | from main terminal 2 to external heatsink; $f = 1\text{ MHz}$; $T_h = 25\text{ }^\circ\text{C}$ | - | 10 | - | pF |

11. Characteristics

Table 8. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|------|-----|-----|------|
| Static characteristics | | | | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7 | - | - | 50 | mA |
| | | V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7 | - | - | 50 | mA |
| | | V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7 | - | - | 50 | mA |
| I _L | latching current | V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8 | - | - | 60 | mA |
| | | V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8 | - | - | 90 | mA |
| | | V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8 | - | - | 60 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; Fig. 9 | - | - | 60 | mA |
| V _T | on-state voltage | I _T = 24 A; T _j = 25 °C; Fig. 10 | - | 1.2 | 1.5 | V |
| V _{GT} | gate trigger voltage | V _D = 12 V; T _j = 25 °C; Fig. 11 | - | 0.7 | 1 | V |
| | | V _D = 400 V; T _j = 150 °C; Fig. 11 | 0.2 | 0.4 | - | V |
| I _D | off-state current | V _D = 800 V; T _j = 150 °C | - | 0.2 | 1 | mA |
| Dynamic characteristics | | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit | 1800 | - | - | V/μs |
| dI _{com} /dt | rate of change of commutating current | V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 20 A; dV _{com} /dt = 10 V/μs; gate open circuit | 25 | - | - | A/ms |
| | | V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 20 A; dV _{com} /dt = 1 V/μs; gate open circuit | 65 | - | - | A/ms |



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

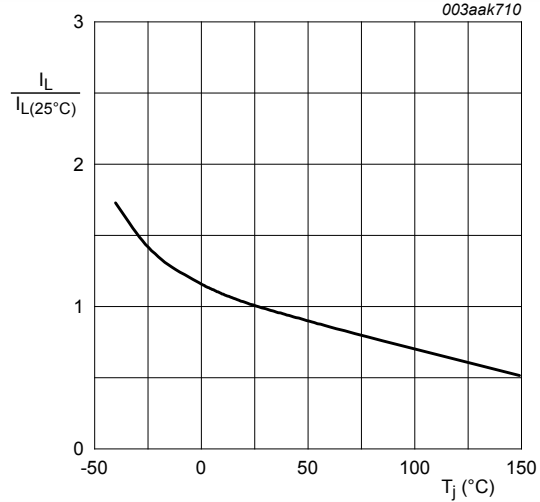


Fig. 8. Normalized latching current as a function of junction temperature

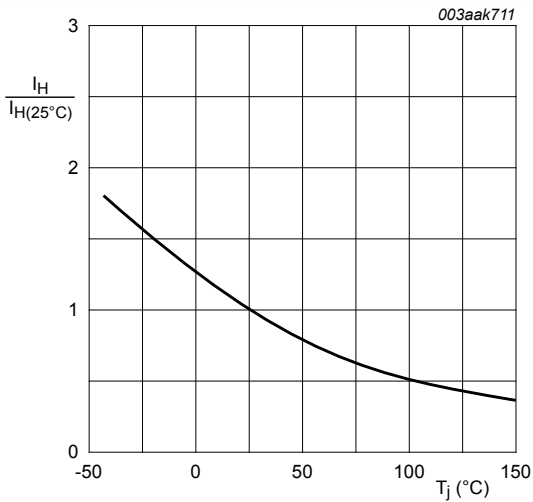
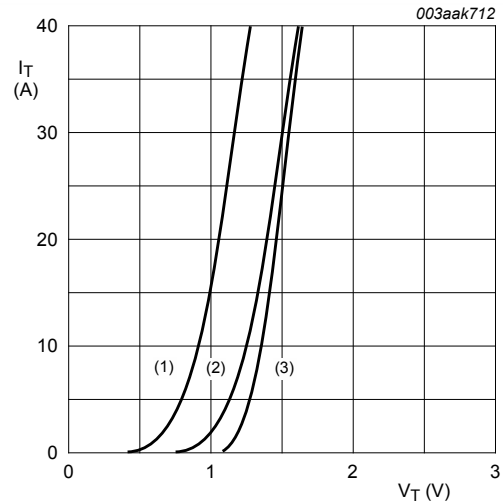


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.087 \text{ V}; R_s = 0.014 \Omega$

- (1) $T_j = 150^{\circ}\text{C}$; typical values
- (2) $T_j = 150^{\circ}\text{C}$; maximum values
- (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

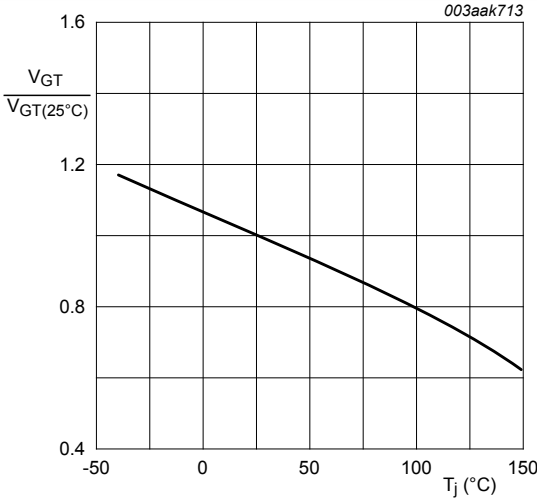


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline



Fig. 12. Package outline TO-220F (SOT186A)

13. Legal information

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|--------------------------------|--------------------|---|
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